

BDP949H6327XTSA1

BDP949H6327XTSA1 Information



t Number	BDP949H6327XTSA1
nufacturer	Infineon Technologies
egory	Discrete Semiconductor Products Transistors - Bipolar (BJT) - Single
cription	TRANS NPN 60V 3A SOT223
kage	TO-261-4, TO-261AA
	For the pricing/inventory/lead time, please contact us Website: https://www.heisener.com E-mail: salesdept@heisener.com



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BDP949H6327XTSA1 Specifications

Manufacturer Part NumberBDP949H6327XTSA1ManufacturerInfineon TechnologiesCategoryDiscrete Semiconductor ProductsTransistor PackageTo-261-4, TO-261AASeries-Transistor TypeNPNCurrent - Collector (Ic) (Max)GOVVoltage - Collector Emitter Breakdown (Max)60VVcc Saturation (Max) @ Ib, Ic500mV @ 200mA, 2ACurrent - Collector Cutoff (Max)100nA (ICBO)DC Current Gain (hFE) (Min) @ Ic, Vce100 @ 500mA, 1VPower - Max5WFrequency - Transition100MHzOperating Temperature150°C (TJ)Mounting TypeSurface MountPackage / CaseTO-261-4, TO-261AA		
CategoryDiscrete Semiconductor Products Transistors - Bipolar (BJT) - SinglePackageTO-261-4, TO-261AASeries-Transistor TypeNPNCurrent - Collector (Ic) (Max)3AVoltage - Collector Emitter Breakdown (Max)60VVce Saturation (Max) @ Ib, Ic500mV @ 200mA, 2ACurrent - Collector Cutoff (Max)100nA (ICBO)DC Current Gain (hFE) (Min) @ Ic, Vce100 @ 500mA, 1VPower - Max5WFrequency - Transition100MHzOperating Temperature150°C (TJ)Mounting TypeSurface Mount	Part Number	BDP949H6327XTSA1
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PackageTO-261-4, TO-261AASeries-Transistor TypeNPNCurrent - Collector (Ic) (Max)3AVoltage - Collector Emitter Breakdown (Max)60VVce Saturation (Max) @ Ib, Ic500mV @ 200mA, 2ACurrent - Collector Cutoff (Max)100nA (ICBO)DC Current Gain (hFE) (Min) @ Ic, Vce100 @ 500mA, 1VPower - Max5WFrequency - Transition100MHzOperating Temperature150°C (TJ)Mounting TypeSurface Mount		Discrete Semiconductor Products
Series-Transistor TypeNPNCurrent - Collector (Ic) (Max)3AVoltage - Collector Emitter Breakdown (Max)60VVce Saturation (Max) @ Ib, Ic500mV @ 200mA, 2ACurrent - Collector Cutoff (Max)100nA (ICBO)DC Current Gain (hFE) (Min) @ Ic, Vce100 @ 500mA, 1VPower - Max5WFrequency - Transition100MHzOperating Temperature150°C (TJ)Mounting TypeSurface Mount		Transistors - Bipolar (BJT) - Single
Transistor TypeNPNCurrent - Collector (Ic) (Max)3AVoltage - Collector Emitter Breakdown (Max)60VVcc Saturation (Max) @ Ib, Ic500mV @ 200mA, 2ACurrent - Collector Cutoff (Max)100nA (ICBO)DC Current Gain (hFE) (Min) @ Ic, Vce100 @ 500mA, 1VPower - Max5WFrequency - Transition100MHzOperating Temperature150°C (TJ)Mounting TypeSurface Mount		TO-261-4, TO-261AA
Current - Collector (Ic) (Max)3AVoltage - Collector Emitter Breakdown (Max)60VVce Saturation (Max) @ Ib, Ic500mV @ 200mA, 2ACurrent - Collector Cutoff (Max)100nA (ICBO)DC Current Gain (hFE) (Min) @ Ic, Vce100 @ 500mA, 1VPower - Max5WFrequency - Transition100MHzOperating Temperature150°C (TJ)Mounting TypeSurface Mount		-
Voltage - Collector Emitter Breakdown (Max)60VVce Saturation (Max) @ Ib, Ic500mV @ 200mA, 2ACurrent - Collector Cutoff (Max)100nA (ICBO)DC Current Gain (hFE) (Min) @ Ic, Vce100 @ 500mA, 1VPower - Max5WFrequency - Transition100MHzOperating Temperature150°C (TJ)Mounting TypeSurface Mount	pe	NPN
Vce Saturation (Max) @ Ib, Ic500mV @ 200mA, 2ACurrent - Collector Cutoff (Max)100nA (ICBO)DC Current Gain (hFE) (Min) @ Ic, Vce100 @ 500mA, 1VPower - Max5WFrequency - Transition100MHzOperating Temperature150°C (TJ)Mounting TypeSurface Mount	lector (Ic) (Max)	3A
Current - Collector Cutoff (Max)100nA (ICBO)DC Current Gain (hFE) (Min) @ Ic, Vce100 @ 500mA, 1VPower - Max5WFrequency - Transition100MHzOperating Temperature150°C (TJ)Mounting TypeSurface Mount	lector Emitter Breakdown (Max)	60V
DC Current Gain (hFE) (Min) @ Ic, Vce100 @ 500mA, 1VPower - Max5WFrequency - Transition100MHzOperating Temperature150°C (TJ)Mounting TypeSurface Mount	on (Max) @ Ib, Ic	500mV @ 200mA, 2A
Power - Max5WFrequency - Transition100MHzOperating Temperature150°C (TJ)Mounting TypeSurface Mount	lector Cutoff (Max)	100nA (ICBO)
Frequency - Transition100MHzOperating Temperature150°C (TJ)Mounting TypeSurface Mount	Gain (hFE) (Min) @ Ic, Vce	100 @ 500mA, 1V
Operating Temperature150°C (TJ)Mounting TypeSurface Mount		5W
Mounting Type Surface Mount	Fransition	100MHz
	mperature	150°C (TJ)
Package / Case TO 261.4 TO 261.4 A	pe	Surface Mount
10-201-4, 10-201AA	se	TO-261-4, TO-261AA
Supplier Device Package PG-SOT223-4	ice Package	PG-SOT223-4
R		Report errors?

BDP949H6327XTSA1 Guarantees



Quality Guarantees

We provide 90 days warranty. * If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction. Our experienced sales team and tech support team back our services to satisfy all our customers.

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